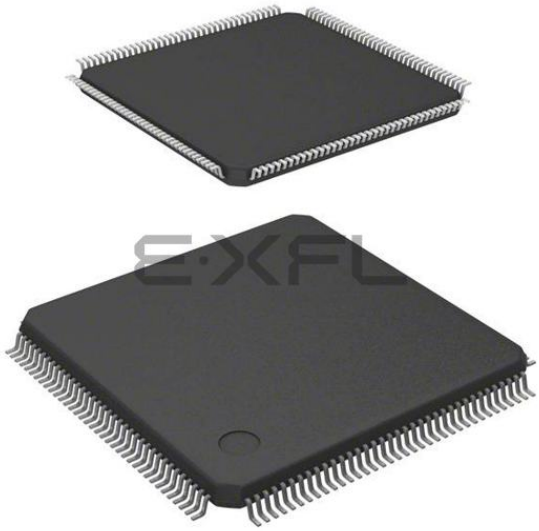

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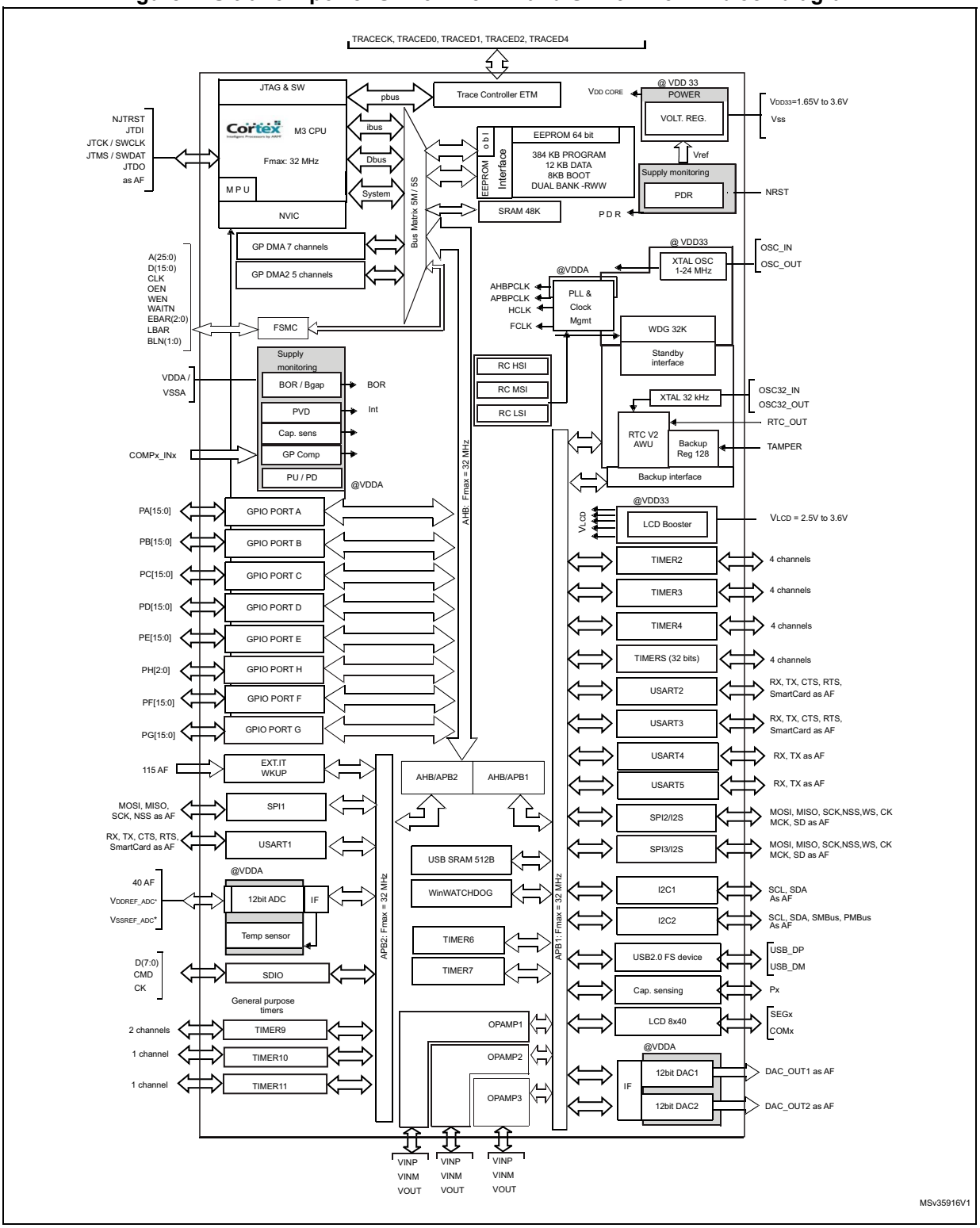
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, POR, PWM, WDT
Number of I/O	115
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	12K x 8
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 40x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151zdt6

List of figures

3 Functional overview

Figure 1. Ultra-low-power STM32L151xD and STM32L152xD block diagram



operate. This acquisition is managed directly by the GPIOs, timers and analog I/O groups (see *Section 3.15: System configuration controller and routing interface*).

Reliable touch sensing functionality can be quickly and easily implemented using the free STM32L1xx STMTouch touch sensing firmware library.

3.17 Timers and watchdogs

The ultra-low-power STM32L151xD and STM32L152xD devices include seven general-purpose timers, two basic timers, and two watchdog timers.

Table 6 compares the features of the general-purpose and basic timers.

Table 6. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3, TIM4	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM5	32-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM9	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.17.1 General-purpose timers (TIM2, TIM3, TIM4, TIM5, TIM9, TIM10 and TIM11)

There are seven synchronizable general-purpose timers embedded in the STM32L151xD and STM32L152xD devices (see *Table 6* for differences).

TIM2, TIM3, TIM4, TIM5

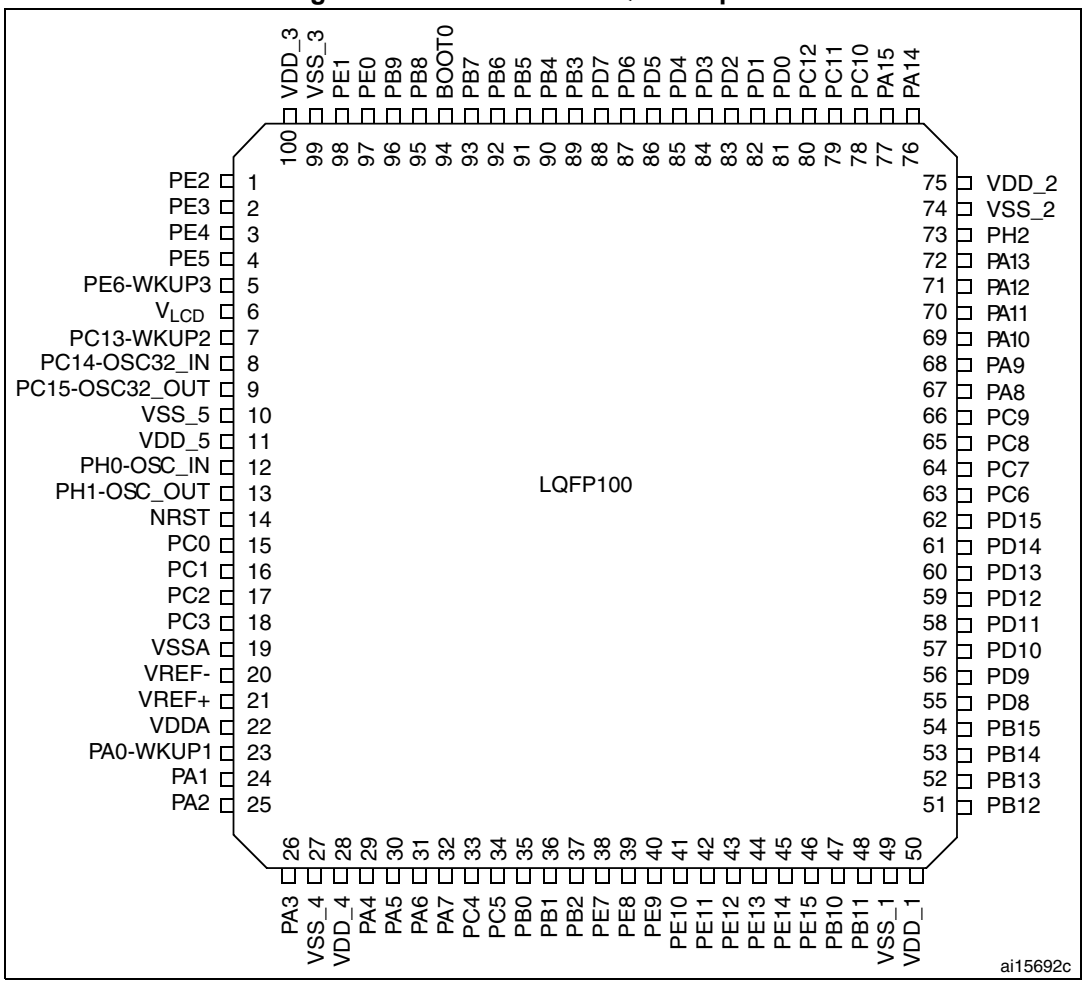
TIM2, TIM3, TIM4 are based on 16-bit auto-reload up/down counter. TIM5 is based on a 32-bit auto-reload up/down counter. They include a 16-bit prescaler. They feature four independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input captures/output compares/PWMs on the largest packages.

TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together or with the TIM10, TIM11 and TIM9 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Figure 5. STM32L15xVD LQFP100 pinout



1. This figure shows the package top view.

Table 8. STM32L151xD and STM32L152xD pin definitions (continued)

Pins					Pin name	Pin Type(1)	I / O structure	Main function(2) (after reset)	Pin functions	
LQFP144	UFBGA132	LQFP100	LQFP64	WLCSP64					Alternate functions	Additional functions
14	F3	-	-	-	PF4	I/O	FT	PF4	FSMC_A4	-
15	F4	-	-	-	PF5	I/O	FT	PF5	FSMC_A5	-
16	F2	10	-	-	V_{SS_5}	S	-	V_{SS_5}	-	-
17	G2	11	-	-	V_{DD_5}	S	-	V_{DD_5}	-	-
18	G3	-	-	-	PF6	I/O	FT	PF6	TIM5_CH1/TIM5_ETR	ADC_IN27
19	G4	-	-	-	PF7	I/O	FT	PF7	TIM5_CH2	ADC_IN28/ COMP1_INP
20	H4	-	-	-	PF8	I/O	FT	PF8	TIM5_CH3	ADC_IN29/ COMP1_INP
21	J6	-	-	-	PF9	I/O	FT	PF9	TIM5_CH4	ADC_IN30/ COMP1_INP
22	-	-	-	-	PF10	I/O	FT	PF10	-	ADC_IN31/ COMP1_INP
23	F1	12	5	D8	PH0-OSC_IN(5)	I/O	TC	PH0	-	OSC_IN
24	G1	13	6	D7	PH1-OSC_OUT(5)	I/O	TC	PH1	-	OSC_OUT
25	H2	14	7	C7	NRST	I/O	RST	NRST	-	-
26	H1	15	8	E8	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP
27	J2	16	9	F8	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP OPAMP3_VINP
28	-	17	10	D6	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP OPAMP3_VINM
-	J3	-	-	-	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
-	K1	-	-	-	OPAMP3_VINM	I	-	OPAMP3_VINM	-	-
29	K2	18	11	F7	PC3	I/O	TC	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP/ OPAMP3_VOUT
30	J1	19	12	E7	V_{SSA}	S	-	V_{SSA}	-	-

6.1.6 Power supply scheme

Figure 11. Power supply scheme

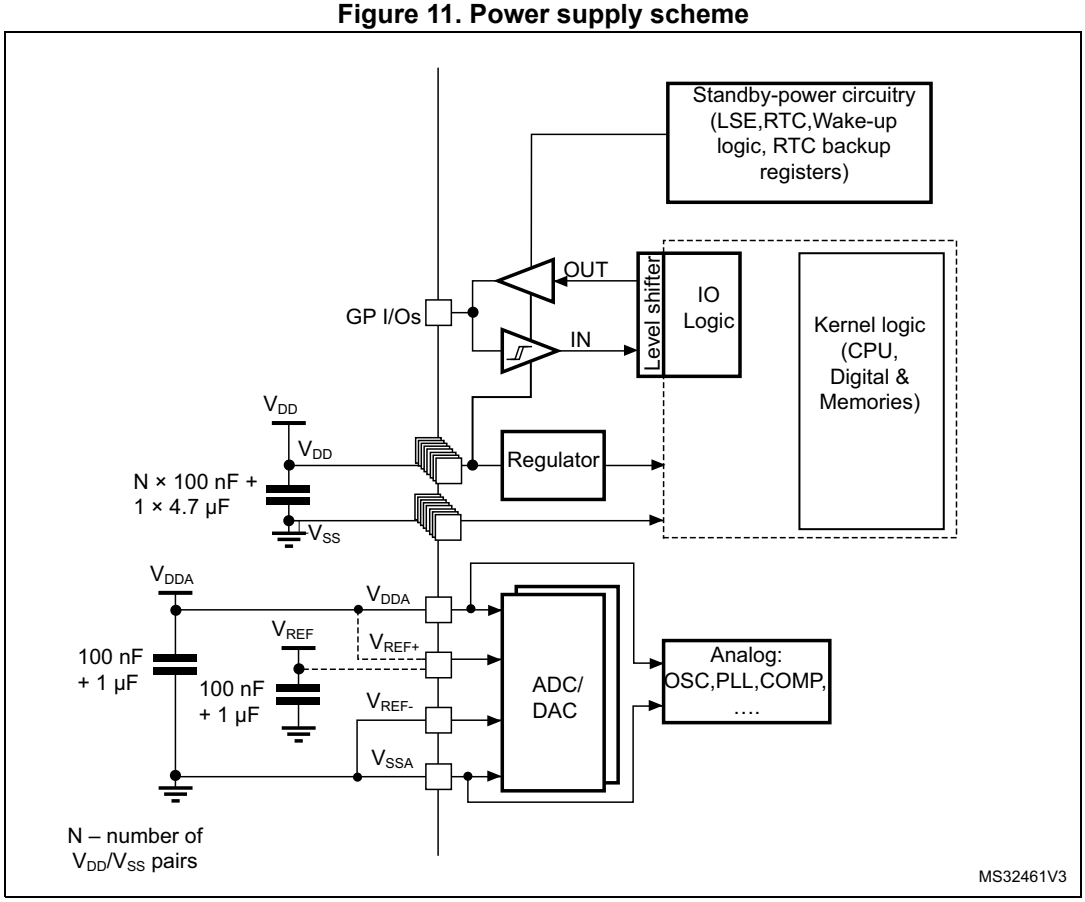


Table 13. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
T_J	Junction temperature range	6 suffix version	–40	105	°C
		7 suffix version	–40	110	

1. When the ADC is used, refer to *Table 64: ADC characteristics*.
2. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up .
3. To sustain a voltage higher than VDD+0.3V, the internal pull-up/pull-down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see *Table 80: Thermal characteristics on page 145*).
5. In low-power dissipation state, T_A can be extended to -40°C to 105°C temperature range as long as T_J does not exceed T_J max (see *Table 80: Thermal characteristics on page 145*).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the conditions summarized in *Table 13*.

Table 14. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}(1)	V_{DD} rise time rate	BOR detector enabled	0	-	∞	µs/V
		BOR detector disabled	0	-	1000	
	V_{DD} fall time rate	BOR detector enabled	20	-	∞	
		BOR detector disabled	0	-	1000	
$T_{RSTTEMPO}$(1)	Reset temporization	V_{DD} rising, BOR enabled	-	2	3.3	ms
		V_{DD} rising, BOR disabled(2)	0.4	0.7	1.6	
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1	1.5	1.65	V
		Rising edge	1.3	1.5	1.65	
V_{BOR0}	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	
		Rising edge	1.69	1.76	1.8	
V_{BOR1}	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.03	2.07	
V_{BOR2}	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
		Rising edge	2.31	2.41	2.44	

6.3.3 Embedded internal reference voltage

The parameters given in *Table 16* are based on characterization results, unless otherwise specified.

Table 15. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00F8 - 0x1FF8 00F9

Table 16. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}$ (1)	Internal reference voltage	– 40 °C < T_J < +110 °C	1.202	1.224	1.242	V
I_{REFINT}	Internal reference current consumption	-	-	1.4	2.3	µA
$T_{VREFINT}$	Internal reference startup time	-	-	2	3	ms
V_{VREF_MEAS}	V_{DDA} and V_{REF+} voltage during V_{REFINT} factory measure	-	2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REF} value(2)	Including uncertainties due to ADC and V_{DDA}/V_{REF+} values	-	-	±5	mV
T_{Coeff}(3)	Temperature coefficient	–40 °C < T_J < +110 °C	-	25	100	ppm/°C
A_{Coeff}(3)	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
$V_{DDCoeff}$(3)	Voltage coefficient	3.0 V < V_{DDA} < 3.6 V	-	-	2000	ppm/V
$T_{S\_vrefint}$(3)	ADC sampling time when reading the internal reference voltage	-	4	-	-	µs
T_{ADC_BUF}(3) (4)	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
I_{BUF_ADC}(3)	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
I_{VREF_OUT}(3)	VREF_OUT output current (5)	-	-	-	1	µA
C_{VREF_OUT}(3)	VREF_OUT output load	-	-	-	50	pF
I_{LPBUF}(3)	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V_{REFINT_DIV1}(3)	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}(3)	1/2 reference voltage	-	49	50	51	
V_{REFINT_DIV3}(3)	3/4 reference voltage	-	74	75	76	

1. Guaranteed by test in production.
2. The internal V_{REF} value is individually measured in production and stored in dedicated EEPROM bytes.
3. Guaranteed by characterization results.
4. Shortest sampling time can be determined in the application by multiple iterations.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register)

Table 20. Current consumption in Low-power run mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
$I_{DD\ (LP\ Run)}$	Supply current in Low-power run mode	All peripherals OFF, code executed from RAM, Flash switched OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	11	14	µA
				T_A = 85 °C	26	32	
				T_A = 105 °C	53	72	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A =-40 °C to 25 °C	18	21	
				T_A = 85 °C	33	40	
				T_A = 105 °C	60	78	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	36	41	
				T_A = 55 °C	39	44	
				T_A = 85 °C	50	58	
				T_A = 105 °C	78	95	
		All peripherals OFF, code executed from Flash, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	36	40.5	
				T_A = 85 °C	53	60	
				T_A = 105 °C	81	100	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	44	49	
				T_A = 85 °C	61	67	
				T_A = 105 °C	89	107	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	64	71	
				T_A = 55 °C	68	73	
				T_A = 85 °C	80	88	
				T_A = 105 °C	101	110	
I_{DD} max (LP Run)	Max allowed current in Low-power run mode	V_{DD} from 1.65 V to 3.6 V	-	-	-	200	

1. Guaranteed by characterization results, unless otherwise specified.

Table 23. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
I_{DD} (Standby with RTC)	Supply current in Standby mode with RTC enabled	RTC clocked by LSI (no independent watchdog)	T_A = -40 °C to 25 °C V_{DD} = 1.8 V	0.82	-	µA
			T_A = -40 °C to 25 °C	1.15	1.9	
			T_A = 55 °C	1.15	2.2	
			T_A= 85 °C	1.65	4	
			T_A = 105 °C	2.75	8.3(2)	
		RTC clocked by LSE external quartz (no independent watchdog)(3)	T_A = -40 °C to 25 °C V_{DD} = 1.8 V	1.05	-	
			T_A = -40 °C to 25 °C	1.35	-	
			T_A = 55 °C	1.55	-	
			T_A= 85 °C	2.1	-	
			T_A = 105 °C	3.3	-	
I_{DD} (Standby)	Supply current in Standby mode (RTC disabled)	Independent watchdog and LSI enabled	T_A = -40 °C to 25 °C	1	1.7	
		Independent watchdog and LSI OFF	T_A = -40 °C to 25 °C	0.305	0.6	
			T_A = 55 °C	0.365	0.9	
			T_A = 85 °C	0.66	2.75	
			T_A = 105 °C	2	7(2)	
I_{DD} (WU from Standby)	Supply current during wakeup time from Standby mode	-	T_A = -40 °C to 25 °C	1	-	mA

1. Guaranteed by characterization results, unless otherwise specified.
2. Guaranteed by test in production.
3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8pF loading capacitors.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following table. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on

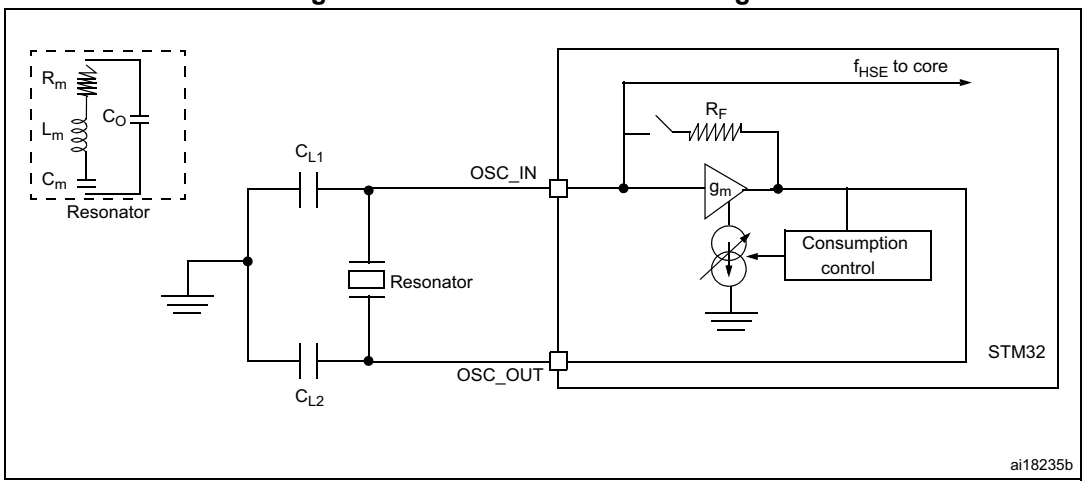
Table 28. HSE oscillator characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	1		24	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 Ω	-	20	-	pF
I_{HSE}	HSE driving current	V_{DD}= 3.3 V, V_{IN} = V_{SS} with 30 pF load	-	-	3	mA
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)	mA
		C = 10 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.46 (stabilized)	
g_m	Oscillator transconductance	Startup	3.5	-	-	mA /V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	1	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by characterization results.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 16*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}. Refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website *www.st.com*.

Figure 16. HSE oscillator circuit diagram



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 29*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 29. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE}	Low speed external oscillator frequency	-	-	32.768	-	kHz
R_F	Feedback resistor	-	-	1.2	-	MΩ
$C^{(2)}$	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 kΩ	-	8	-	pF
I_{LSE}	LSE driving current	V_{DD} = 3.3 V, V_{IN} = V_{SS}	-	-	1.1	µA
$I_{DD\ (LSE)}$	LSE oscillator current consumption	V_{DD} = 1.8 V	-	450	-	nA
		V_{DD} = 3.0 V	-	600	-	
		V_{DD} = 3.6V	-	750	-	
g_m	Oscillator transconductance	-	3	-	-	µA/V
$t_{SU(LSE)}$(4)	Startup time	V_{DD} is stabilized	-	1	-	s

1. Guaranteed by characterization results.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details.

Table 39. Asynchronous multiplexed PSRAM/NOR read timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3*T_{HCLK} - 1.5$	$3*T_{HCLK} + 1$	ns
$t_{v(NOE\_NE)}$	FSMC_NEx low to FSMC_NOE low	$2*T_{HCLK} - 1$	$2*T_{HCLK}$	ns
$t_{w(NOE)}$	FSMC_NOE low time	$T_{HCLK} - 0.5$	$T_{HCLK} + 0.5$	ns
$t_{h(NE\_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	5	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	1.5	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK} - 0.5$	T_{HCLK}	ns
$t_{h(AD\_NADV)}$	FSMC_AD(address) valid hold time after FSMC_NADV high	$T_{HCLK} - 6$	-	ns
$t_{h(A\_NOE)}$	Address hold time after FSMC_NOE high	$2*T_{HCLK} - 1$	-	ns
$t_{h(BL\_NOE)}$	FSMC_BL time after FSMC_NOE high	1.5	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0	ns
$t_{su(Data\_NE)}$	Data to FSMC_NEx high setup time	T_{HCLK}	-	ns
$t_{su(Data\_NOE)}$	Data to FSMC_NOE high setup time	T_{HCLK}	-	ns
$t_{h(Data\_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns

1. C_L = 30 pF.

Figure 21. Asynchronous multiplexed PSRAM/NOR write waveforms

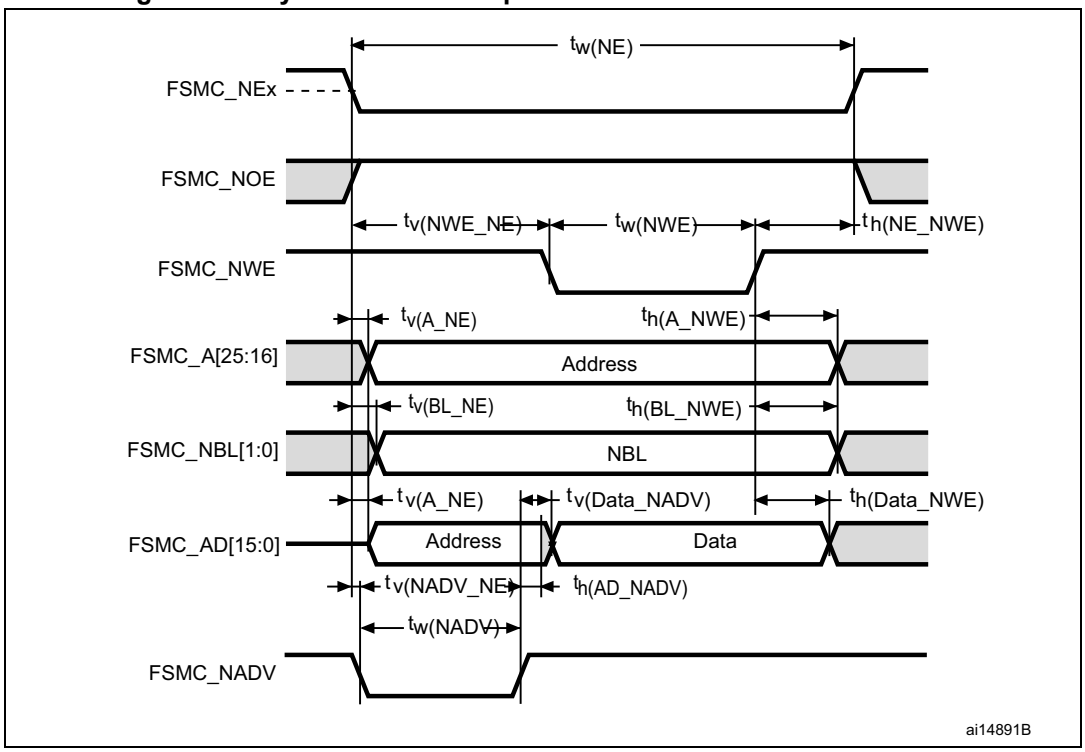


Table 43. Synchronous non-multiplexed NOR/PSRAM read timings(1) (continued)

Symbol	Parameter	Min	Max	Unit
$t_{su(NWAITV-CLKH)}$	FSMC_NWAIT valid before FSMC_CLK high	6	-	ns
$t_{h(CLKH-NWAITV)}$	FSMC_NWAIT valid after FSMC_CLK high	0	-	ns

1. C_L = 30 pF.

Figure 25. Synchronous non-multiplexed PSRAM write timings

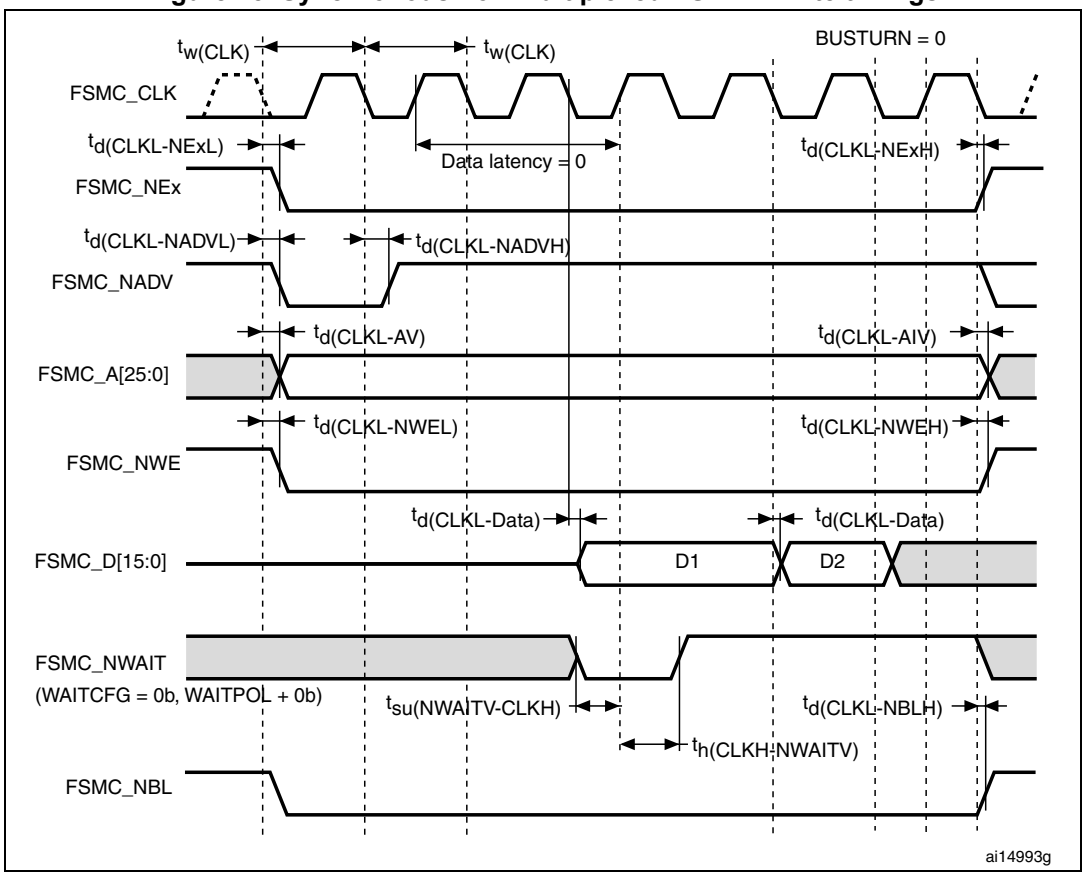


Table 44. Synchronous non-multiplexed PSRAM write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2*T_{HCLK}$ -3	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x = 0...2)	-	0	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x = 0...2)	1	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	5	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	7	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x = 16...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x = 16...25)	T_{HCLK} + 4	-	ns
$t_{d(CLKL-NWEL)}$	FSMC_CLK low to FSMC_NWE low	-	2	ns

Figure 29. SPI timing diagram - slave mode and CPHA = 0

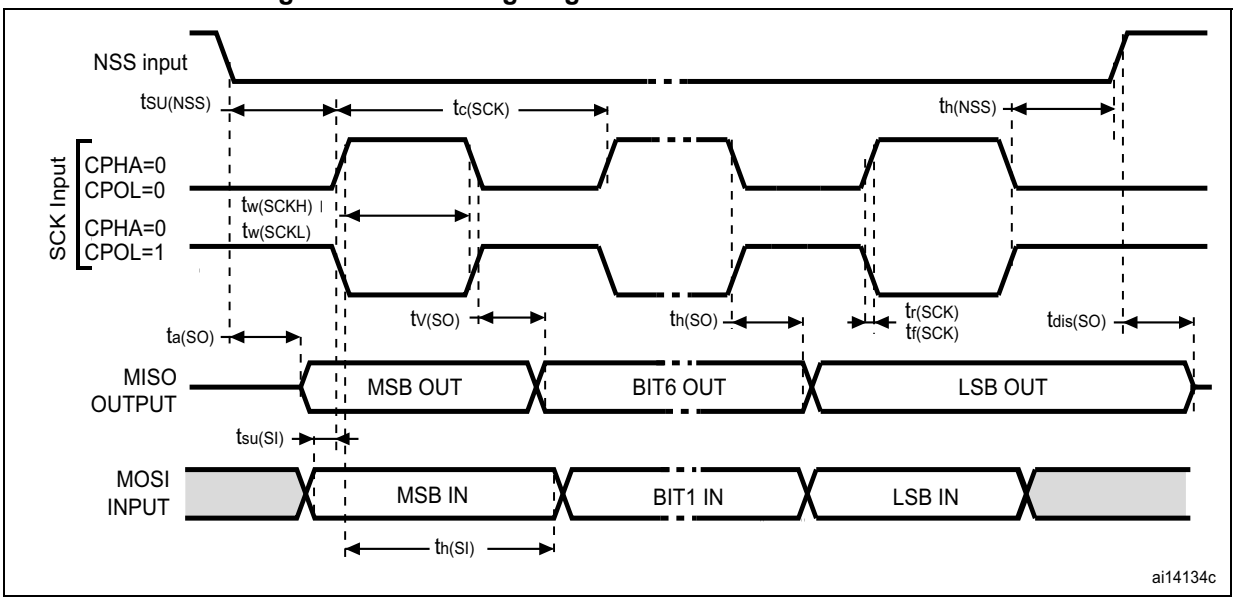
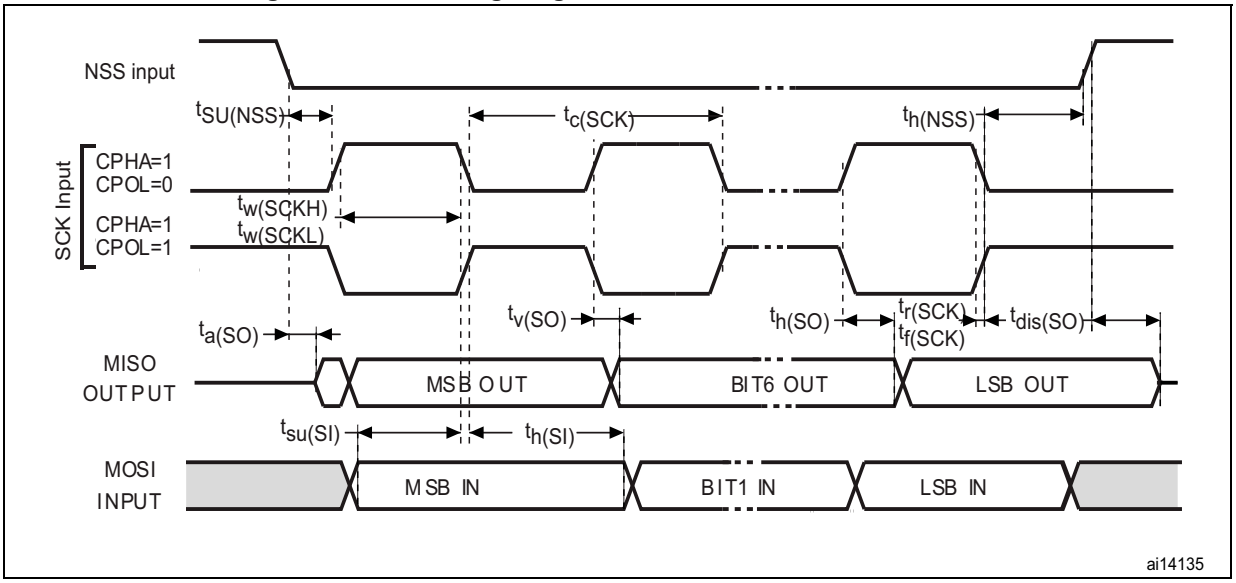
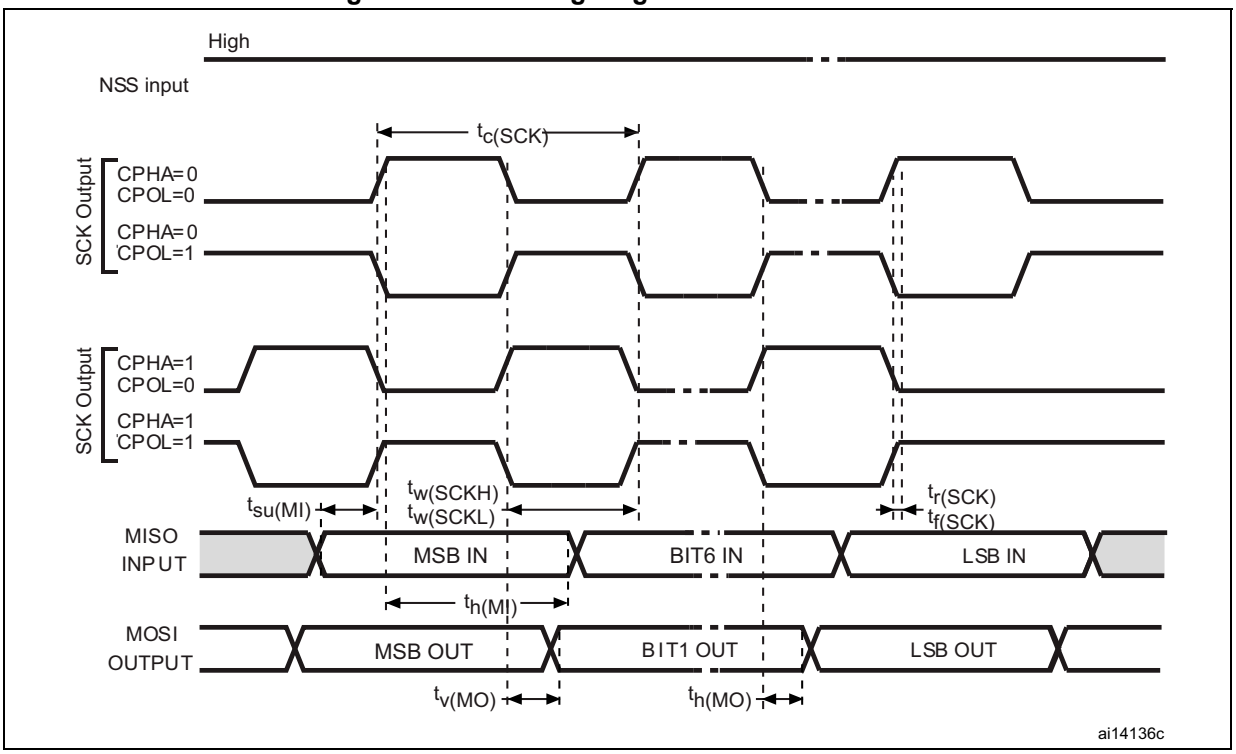


Figure 30. SPI timing diagram - slave mode and CPHA = 1(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 31. SPI timing diagram - master mode(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 68. Operational amplifier characteristics (continued)

Symbol	Parameter		Condition(1)	Min(2)	Typ	Max(2)	Unit
PSRR	Power supply rejection ratio	Normal mode	DC	-	-85	-	dB
		Low-power mode		-	-90	-	
GBW	Bandwidth	Normal mode	V_{DD}>2.4 V	400	1000	3000	kHZ
		Low-power mode		150	300	800	
		Normal mode	V_{DD}<2.4 V	200	500	2200	
		Low-power mode		70	150	800	
SR	Slew rate	Normal mode	V_{DD}>2.4 V (between 0.1 V and V_{DD}-0.1 V)	-	700	-	V/ms
		Low-power mode	V_{DD}>2.4 V	-	100	-	
		Normal mode	V_{DD}<2.4 V	-	300	-	
		Low-power mode		-	50	-	
AO	Open loop gain	Normal mode		55	100	-	dB
		Low-power mode		65	110	-	
R_L	Resistive load	Normal mode	V_{DD}<2.4 V	4	-	-	kΩ
		Low-power mode		20	-	-	
C_L	Capacitive load		-	-	-	50	pF
VOH_{SAT}	High saturation voltage	Normal mode	I_{LOAD} = max or R_L = min	V_{DD}-100	-	-	mV
		Low-power mode		V_{DD}-50	-	-	
VOL_{SAT}	Low saturation voltage	Normal mode		-	-	100	
		Low-power mode		-	-	50	
φm	Phase margin		-	-	60	-	°
GM	Gain margin		-	-	-12	-	dB
$t_{OFFTRIM}$	Offset trim time: during calibration, minimum time needed between two steps to have 1 mV accuracy		-	-	1	-	ms
t_{WAKEUP}	Wakeup time	Normal mode	C_L ≤50 pf, R_L ≥ 4 kΩ	-	10	-	µs
		Low-power mode	C_L ≤50 pf, R_L ≥ 20 kΩ	-	30	-	

1. Operating conditions are limited to junction temperature (0 °C to 105 °C) when V_{DD} is below 2 V. Otherwise to the full ambient temperature range (-40 °C to 85 °C, -40 °C to 105 °C).
2. Guaranteed by characterization results.

6.3.22 Temperature sensor characteristics

Table 69. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FA - 0x1FF8 00FB
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FE - 0x1FF8 00FF

Table 70. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ±5°C(2)	612	626.8	641.5	mV
$I_{DDA(TEMP)}$(3)	Current consumption	-	3.4	6	µA
t_{START}(3)	Startup time	-	-	10	µs
T_{S_temp}(3)	ADC sampling time when reading the temperature	4	-	-	

1. Guaranteed by characterization results.
2. Measured at V_{DD} = 3 V ±10 mV. V110 ADC conversion result is stored in the TS_CAL2 byte.
3. Guaranteed by design.

6.3.23 Comparator

Table 71. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
R_{400K}	R_{400K} value	-	-	400	-	kΩ
R_{10K}	R_{10K} value	-	-	10	-	
V_{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t_{START}	Comparator startup time	-	-	7	10	µs
td	Propagation delay(2)	-	-	3	10	
Voffset	Comparator offset	-	-	±3	±10	mV
$d_{Voffset}/dt$	Comparator offset variation in worst voltage stress conditions	V_{DDA} = 3.6 V V_{IN+} = 0 V V_{IN-} = V_{REFINT} T_A = 25 °C	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption(3)	-	-	160	260	nA

Figure 55. Thermal resistance suffix 6

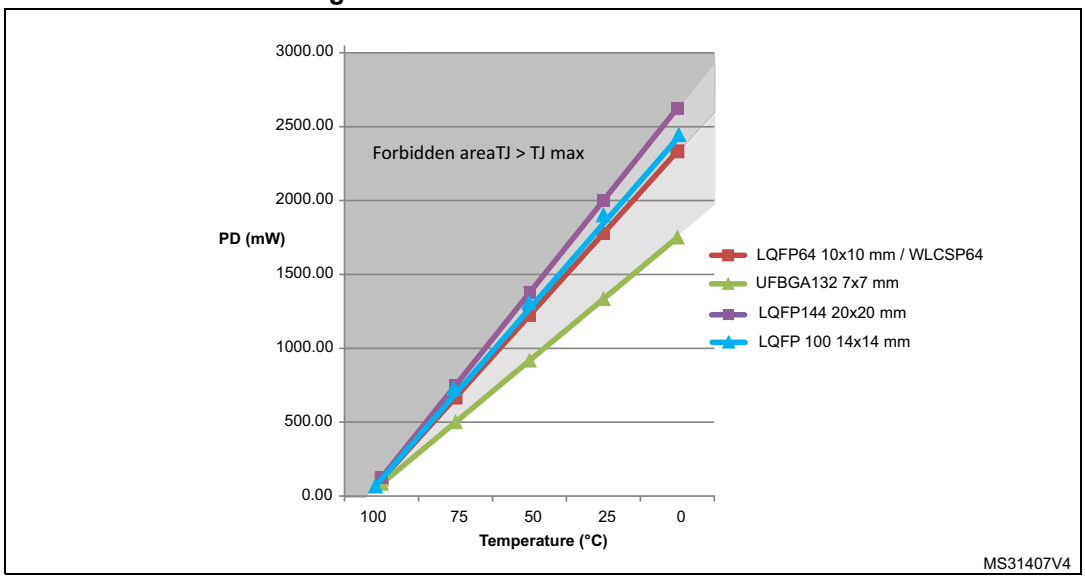
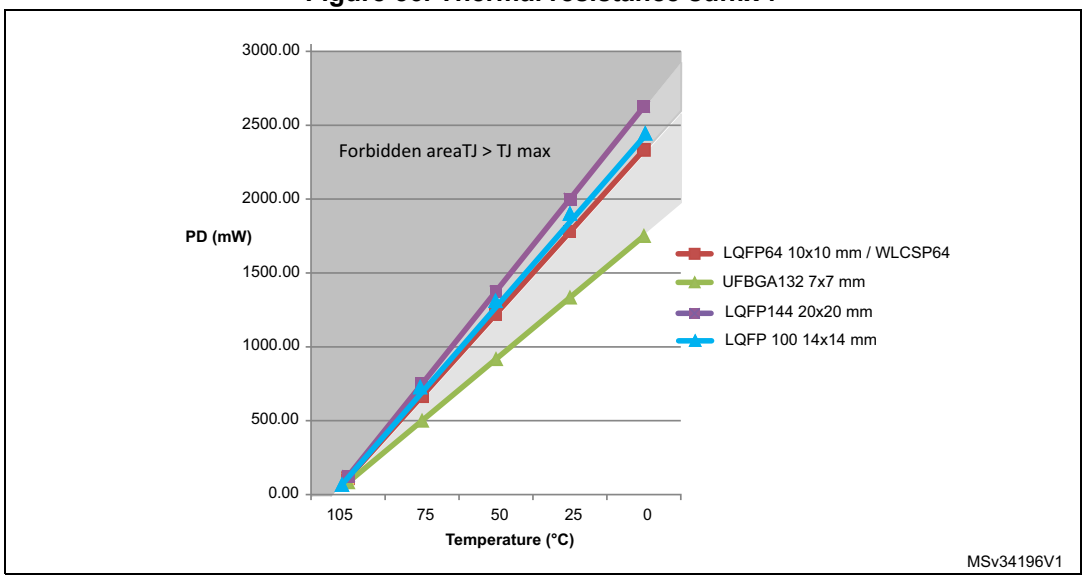


Figure 56. Thermal resistance suffix 7



7.6.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

Table 82. Document revision history (continued)

Date	Revision	Changes
18-Apr-2012	3	Added WLCSP64 package. *Section 3: Functional overview*: changed '128 kHz' to '131 kHz' in section "Low power run mode". *Section 3.17.1: General-purpose timers (TIM2, TIM3, TIM4, TIM5, TIM9, TIM10 and TIM11)*: changed 'six' to 'seven' synchronizable general-purpose timers. *Table 14: STM32L15xxD pin definitions on page 52*: updated name of reference manual in footnote *5.* I2C updated: footnote *3.* from *Table 58* Note about I2C clock updated: footnote *2.* from *Table 58* modified. Note [non-robust] updated: footnote *2.* from *Table 68* modified. GPIOs high current capability updated: *Section 3.6: GPIOs (general-purpose inputs/outputs)* 'except for analog inputs' was removed.
15-Jun-2012	4	Changed maximum number of touch sensing channels to 34, and updated *Table 4: Ultra-low-power STM32L15xxD device features and peripheral counts*. Updated *Section 3.10: ADC (analog-to-digital converter)* to add *Section 3.10.1: Temperature sensor* and *Section 3.10.2: Internal voltage reference (VREFINT)*. Removed caution note below *Figure 8: Power supply scheme*. Added note below *Table 4: STM32L15xQD STM32L162QD UFBGA132 ballout*. Modified *Table 8: STM32L15xRDSTM32L162RD WLCSP64 ballout* to match top view. Changed FSMC_LBAR into FSMC_NADV, and I2C1_SMBAI into I2C1_SMBA in *Table 14: STM32L15xxD pin definitions*. Modified PB10/11/12 for AFIO4 ction, and replaced LBAR by NADV for AFIO12 in *Table 19: ction input/output*. Updated *Table 22: Typical and maximum current consumptions in Stop mode* and added *Note 6*. Updated *Table 23: Typical and maximum current consumptions in Standby mode*. Updated t_{WUSTOP} in *Table :* . Updated *Table 27: Peripheral current consumption*. Updated *Table 60: SPI characteristics*, added *Note 1* and *Note 3*, and applied *Note 2* to $t_{r(SCK)}$, $t_{f(SCK)}$, $t_{w(SCKH)}$, $t_{w(SCKL)}$, $t_{su(MI)}$, $t_{su(SI)}$, $t_{h(MI)}$, and $t_{h(SI)}$. Updated I_{DD} maximum value in *Table 38: Flash memory and data EEPROM characteristics*.